

PCI-EXPRESS GEN 1, GEN 2, & GEN 3 SIX OUTPUT CLOCK GENERATOR

Features

- PCI-Express Gen 1, Gen 2, & Gen 3 compliant
- Low power push-pull type differential output buffers
- Integrated resistors on differential clocks
- Dedicated output enable pin for each clock
- Hardware selectable spread control
- Six PCI-Express clocks

- 25 MHz crystal input or clock input
- I²C support with readback capabilities
- Triangular spread spectrum profile for maximum electromagnetic interference (EMI) reduction
- Industrial temperature:
 40 to 85 °C
- 3.3 V Power supply
- 32-pin QFN package



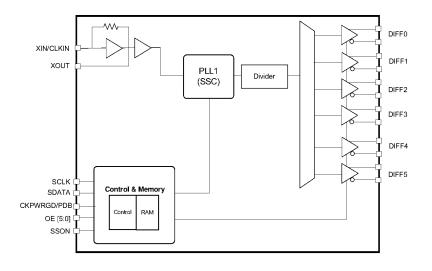
Applications

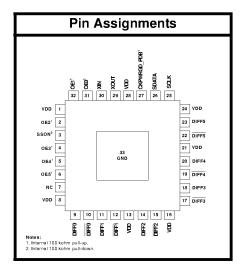
- Network attached storage
- Multi-function printer
- Wireless access point
- Routers

Description

The Si52146 is a spread-controlled PCIe clock generator that can source six PCIe clocks simultaneously. The device has six hardware inputs for enabling the respective outputs on the fly while powered on along with the spread control hardware pin to enable Spread for EMI reduction.

Functional Block Diagram





Patents pending



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1. Electrical Specifications

Table 1. DC Electrical Specifications

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
3.3 V Operating Voltage	VDD core	3.3 ±5%	3.135	3.3	3.465	V
3.3 V Input High Voltage	V _{IH}	Control input pins	2.0	_	V _{DD} + 0.3	V
3.3 V Input Low Voltage	V _{IL}	Control input pins	V _{SS} - 0.3	_	0.8	V
Input High Voltage	V _{IHI2C}	SDATA, SCLK	2.2	_	_	V
Input Low Voltage	V _{ILI2C}	SDATA, SCLK	_	_	1.0	V
Input High Leakage Current	I _{IН}	Except internal pull-down resistors, 0 < V _{IN} < V _{DD}	_	_	5	μА
Input Low Leakage Current	I _{IL}	Except internal pull-up resistors, 0 < V _{IN} < V _{DD}	– 5	_	_	μΑ
3.3 V Output High Voltage (SE)	V _{OH}	I _{OH} = -1 mA	2.4		_	٧
3.3 V Output Low Voltage (SE)	V _{OL}	I _{OL} = 1 mA	_	_	0.4	\ \
High-impedance Output Current	l _{OZ}		–10	_	10	μА
Input Pin Capacitance	C _{IN}		1.5	_	5	pF
Output Pin Capacitance	C _{OUT}		_	_	6	рF
Pin Inductance	L _{IN}		_	_	7	nΗ
Power Down Current	I _{DD_PD}		_	_	1	mA
Dynamic Supply Current	I _{DD_3.3V}	All outputs enabled. Differential clocks with 5" traces and 2 pF load.	_		60	mA

Table 2. AC Electrical Specifications

CLKIN Cycle to Cycle Jitter T _{CCJ} Measured at VDD/2 — 250 ps CLKIN Long Term Jitter T _{LTJ} Measured at VDD/2 — — 350 ps Input High Voltage V _{IH} XIN/CLKIN pin 2 — VDD+0.3 V Input Low Voltage V _{IL} XIN/CLKIN pin — — 0.8 V Input High Current I _{IH} XIN/CLKIN pin, VIN = VDD — — 35 uA Input Low Current I _{IL} XIN/CLKIN pin, VIN = VDD — — 35 uA DIFF at 0.7 V DIFF Duty Cycle T _{DC} Measured at 0 V differential 45 — 55 % Any DIFF Clock Skew from the Earliest Bank to the Latest PLCUS Process of the Cycle Jitter T _{CCJ} Measured at 0 V differential — — 50 ps Output PCle Gen1 REFCLK Phase Jitter RMS _{GEN1} Includes PLL BW 1.5–22 MHz, ζ = 0.54, Td=10 ns, Ftrk=1.5 MHz bank Wh. BER = 1E-12 0 40 108 ps <	Parameter	Symbol	Condition	Min	Тур	Max	Unit
Clock Input CLKIN Duty Cycle T _{DC} Measured at V _{DD} /2 47 — 53 % CLKIN Rise and Fall Times T _R /T _F Measured between 0.2 V _{DD} and 0.5 — 4.0 V/ns CLKIN Cycle to Cycle Jitter T _{CCJ} Measured at VDD/2 — — 250 ps CLKIN Long Term Jitter T _{LTJ} Measured at VDD/2 — — 350 ps Input High Voltage V _{IH} XIN/CLKIN pin 2 — VDD+0.3 V Input Low Voltage V _{IL} XIN/CLKIN pin 2 — VDD+0.3 V Input Low Current I _{IH} XIN/CLKIN pin, VIN = VDD — — 35 uA DIFF at 0.7 V VIL XIN/CLKIN pin, VIN = VDD — — 35 uA DIFF Duty Cycle T _{DC} Measured at 0 V differential 45 — 55 % Any DIFF Clock Skew from the Earliest Bank to the Latest Bank RMSGENI Measured at 0 V differential — 35 50 ps <	Crystal						
CLKIN Duty Cycle T _{DC} Measured at V _{DD} /2 47 — 53 % CLKIN Rise and Fall Times T _R /T _F Measured between 0.2 V _{DD} and 0.8 V _{DD} 0.5 — 4.0 V/ns CLKIN Cycle to Cycle Jitter T _{CCJ} Measured at VDD/2 — — 250 ps CLKIN Long Term Jitter T _{LTJ} Measured at VDD/2 — — 350 ps Input High Voltage V _{IL} XIN/CLKIN pin 2 — VDD+0.3 V Input Low Voltage V _{IL} XIN/CLKIN pin — — 0.8 V Input High Current I _{IL} XIN/CLKIN pin, VIN = VDD — — 35 uA Input How Current I _{IL} XIN/CLKIN pin, VIN = VDD — — 35 uA DIFF 20 CV Cycle To To To MEasured at 0 V differential 45 — 55 % Any DIFF 20 Cx Skew from the Earliest Bank to the Latest Bank To To Cycle Jitter Measured at 0 V differential — — 50 ps <t< td=""><td>Long-term Accuracy</td><td>L_{ACC}</td><td>Measured at V_{DD}/2 differential</td><td>_</td><td>_</td><td>250</td><td>ppm</td></t<>	Long-term Accuracy	L _{ACC}	Measured at V _{DD} /2 differential	_	_	250	ppm
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Clock Input					•	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	CLKIN Duty Cycle	T _{DC}	Measured at V _{DD} /2	47	_	53	%
CLKIN Long Term Jitter T _{LTJ} Measured at VDD/2 — — 350 ps Input High Voltage V _{IH} XIN/CLKIN pin 2 — VDD+0.3 V Input Low Voltage V _{IL} XIN/CLKIN pin — — 0.8 V Input High Current I _{IH} XIN/CLKIN pin, VIN = VDD — — 35 uA Input Low Current I _{IL} XIN/CLKIN pin, VIN = VDD — — 35 uA Input Low Current I _{IL} XIN/CLKIN pin, VIN = VDD — — 35 uA Input Low Current I _{IL} XIN/CLKIN pin, VIN = VDD — — 35 uA Input Polous Current I _{IL} XIN/CLKIN pin, VIN = VDD — — 35 uA Input Polous Current I _{IL} XIN/CLKIN pin, VIN = VDD — — 55 % Any DIFF Cuty Cycle T _C Measured at 0 V differential 45 — 55 % Any DIFF Clock Skew from the Earliest Bank to the Latest<	CLKIN Rise and Fall Times			0.5	_	4.0	V/ns
Input High Voltage	CLKIN Cycle to Cycle Jitter	T _{CCJ}	Measured at VDD/2	_	<u> </u>	250	ps
Input Low Voltage	CLKIN Long Term Jitter	T _{LTJ}	Measured at VDD/2	_	_	350	ps
Input High Current	Input High Voltage	V _{IH}	XIN/CLKIN pin	2	_	VDD+0.3	V
Input Low Current	Input Low Voltage	V _{IL}	XIN/CLKIN pin	_	_	0.8	V
DIFF at 0.7 V DIFF Duty Cycle T _{DC} Measured at 0 V differential 45 — 55 % Any DIFF Clock Skew from the Earliest Bank to the Latest Bank T _{SKEW(win dow)} Measured at 0 V differential — — 50 ps DIFF Cycle to Cycle Jitter T _{CCJ} Measured at 0 V differential — — 50 ps Output PCle Gen1 REFCLK Phase Jitter RMS _{GEN1} Includes PLL BW 1.5–22 MHz, ∠ = 0.54, Td=10 ns, Ftrk=1.5 MHz with BER = 1E-12 0 40 108 ps Output PCle Gen2 REFCLK Phase Jitter RMS _{GEN2} Includes PLL BW 8–16 MHz, Jitter Peaking = 3 dB, ∠ = 0.54, Td=1.5 MHz 0 2 3.0 ps Output PCle Gen2 REFCLK Phase Jitter RMS _{GEN2} Includes PLL BW 8–16 MHz, Jitter Peaking = 3 dB, ∠ = 0.54, Td=12 ns), High Band, 1.5 MHz < F < Nyquist	Input High Current	l _{IH}	XIN/CLKIN pin, VIN = VDD	_	_	35	uA
DIFF Duty Cycle	Input Low Current	I _{IL}	XIN/CLKIN pin, 0 < VIN <0.8	-35	_	_	uA
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	DIFF at 0.7 V			•	•	•	•
Earliest Bank to the Latest Bank dow) dow) dow) dow) DIFF Cycle to Cycle Jitter T _{CCJ} Measured at 0 V differential — 35 50 ps Output PCle Gen1 REFCLK Phase Jitter RMS _{GEN1} Includes PLL BW 1.5–22 MHz, ζ = 0.54, Td=10 ns, Ftrk=1.5 MHz with BER = 1E-12 0 40 108 ps Output PCle Gen2 REFCLK Phase Jitter RMS _{GEN2} Includes PLL BW 8–16 MHz, Jitter Peaking = 3 dB, ζ = 0.54, Td=12 ns), Low Band, F < 1.5 MHz	DIFF Duty Cycle	T _{DC}	Measured at 0 V differential	45	-	55	%
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Earliest Bank to the Latest		Measured at 0 V differential	_	_	50	ps
Phase Jitter ζ = 0.54, Td=10 ns, Ftrk=1.5 MHz with BER = 1E-12 Secondary of the property of the prop	DIFF Cycle to Cycle Jitter	T _{CCJ}	Measured at 0 V differential	_	35	50	ps
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		RMS _{GEN1}	ζ = 0.54, Td=10 ns,	0	40	108	ps
Phase Jitter $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		RMS _{GEN2}	Peaking = 3 dB, ζ = 0.54,	0	2	3.0	ps
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	•	RMS _{GEN2}	Peaking = 3 dB, ζ = 0.54, Td=12 ns), High Band,	0	2	3.1	ps
DIFF Rising/Falling Slew Rate		RMS _{GEN3}	· · · · · · · · · · · · · · · · · · ·	0	0.5	1.0	ps
Voltage High V _{HIGH} — — 1.15 V Voltage Low V _{LOW} — — V Crossing Point Voltage at 0.7 V Swing V _{OX} 300 — 550 mV Enable/Disable and Setup — — — 1.8 ms Clock Stabilization from Power-up T _{STABLE} — — 1.8 ms	DIFF Long Term Accuracy	L _{ACC}	Measured at 0 V differential	_	_	100	ppm
Voltage Low V _{LOW} -0.3 V Crossing Point Voltage at 0.7 V Swing 300 - 550 mV Enable/Disable and Setup Clock Stabilization from Power-up T _{STABLE} - 1.8 ms	DIFF Rising/Falling Slew Rate	T _R /T _F		1	_	8	V/ns
Voltage Low V _{LOW} -0.3 - V Crossing Point Voltage at 0.7 V Swing V _{OX} 300 - 550 mV Enable/Disable and Setup Clock Stabilization from Power-up T _{STABLE} - - - 1.8 ms	Voltage High	V_{HIGH}		_	_	1.15	V
0.7 V Swing Enable/Disable and Setup Clock Stabilization from Power-up TSTABLE TSTABLE TSTABLE	Voltage Low			-0.3	<u> </u>	_	V
Clock Stabilization from Power-up TSTABLE TSTABLE T 1.8 ms		V _{OX}		300	_	550	mV
Power-up	Enable/Disable and Setup			•	•	•	
Stopclock Set-up Time T _{SS} 10.0 — ns		T _{STABLE}		_	_	1.8	ms
	Stopclock Set-up Time	T _{SS}		10.0	_	_	ns

Table 3. Absolute Maximum Conditions

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Main Supply Voltage	V _{DD_3.3V}	Functional	_	_	4.6	V
Input Voltage	V _{IN}	Relative to V _{SS}	-0.5	_	4.6	V _{DC}
Temperature, Storage	T _S	Non-functional	-65	_	150	°C
Temperature, Operating Ambient	T _A	Functional	-40	_	85	°C
Temperature, Junction	TJ	Functional	_	_	150	°C
Dissipation, Junction to Case	Ø _{JC}	JEDEC (JESD 51)	_	_	17	°C/W
Dissipation, Junction to Ambient	Ø _{JA}	JEDEC (JESD 51)	_	_	35	°C/W
ESD Protection (Human Body Model)	ESD _{HBM}	JEDEC (JESD 22-A114)	2000	_	_	V
Flammability Rating	UL-94	UL (Class)		V-0		
Moisture Sensitivity Level	MSL	JEDEC (J-STD-020)		2		

Note: While using multiple power supplies, the voltage on any input or I/O pin cannot exceed the power pin during power-up. Power supply sequencing is not required.



2. Functional Description

2.1. Crystal Recommendations

The clock device requires a parallel resonance crystal. Substituting a series resonance crystal causes the clock device to operate at the wrong frequency and violates the ppm specification. For most applications there is a 300 ppm frequency shift between series and parallel crystals due to incorrect loading.

Table 4. Crystal Recommendations

Frequency (Fund)	Cut	Loading	Load Cap	Shunt Cap (max)	Motional (max)	Tolerance (max)	Stability (max)	Aging (max)
25 MHz	AT	Parallel	12–15 pF	5 pF	0.016 pF	35 ppm	30 ppm	5 ppm

2.1.1. Crystal Loading

Crystal loading plays a critical role in achieving low ppm performance. To realize low ppm performance, use the total capacitance the crystal sees to calculate the appropriate capacitive loading (CL).

Figure 1 shows a typical crystal configuration using the two trim capacitors. It is important that the trim capacitors are in series with the crystal. It is not true that load capacitors are in parallel with the crystal and are approximately equal to the load capacitance of the crystal.

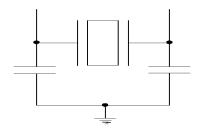


Figure 1. Crystal Capacitive Clarification

2.1.2. Calculating Load Capacitors

In addition to the standard external trim capacitors, consider the trace capacitance and pin capacitance to calculate the crystal loading correctly. Again, the capacitance on each side is in series with the crystal. The total capacitance on both side is twice the specified crystal load capacitance (CL). Trim capacitors are calculated to provide equal capacitive loading on both sides.

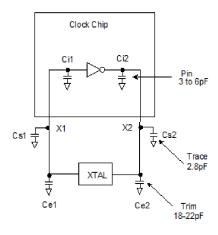


Figure 2. Crystal Loading Example



Si52146

Use the following formulas to calculate the trim capacitor values for Ce1 and Ce2.

Load Capacitance (each side)

$$Ce = 2 \times CL - (Cs + Ci)$$

Total Capacitance (as seen by the crystal)

CLe =
$$\frac{1}{(\frac{1}{Ce1 + Cs1 + Ci1} + \frac{1}{Ce2 + Cs2 + Ci2})}$$

- CL: Crystal load capacitance
- CLe: Actual loading seen by crystal using standard value trim capacitors
- Ce: External trim capacitors
- Cs: Stray capacitance (terraced)
- Ci : Internal capacitance (lead frame, bond wires, etc.)

2.2. CKPWRGD_PDB (Power down) Clarification

The CKPWRGD_PDB pin is a dual-function pin. During initial power up, the pin functions as CKPWRGD. Upon the first powerup if the CKPWRGD is low, the device outputs will be disabled, but the crystal oscillator and I²C logics are active. Once CKPWRGD has been sampled high by the clock chip, the pin assumes a PDB functionality. When the pin has assumed a PDB functionality and the pin is pull low, the device will be placed in standby mode.

2.3. PDB (Power down) Assertion

The PDB pin is an asynchronous active low input used to disable all clocks in a glitch free manner. All outputs will be driven low in power down mode. In power down mode, all outputs, the crystal oscillator and the I²C logic are disabled.

2.4. PDB Deassertion

When a valid rising edge on CKPWRGD/PDB pin is applied, all outputs are enabled in a glitch free manner within two to six output clock cycle.

2.5. OE Clarification

The OE pins are active high inputs used to enable and disable the output clocks. To enable the output clock, the OE pin needs to be logic high and the I^2C output enable bit needs to be logic high. There are two methods to disable the output clocks: the OE is pulled to a logic low, or the I^2C enable bit is set to a logic low. The OE pins is required to be driven at all time and even though it has an internally $100 \text{ k}\Omega$ resistor.

2.6. OE Assertion

The OE signals are active high input used for synchronous stopping and starting the DIFF output clocks respectively while the rest of the clock generator continues to function. The assertion of the OE signal by making it logic high causes stopped respective DIFF output to resume normal operation. No short or stretched clock pulses are produced when the clock resumes. The maximum latency from the assertion to active outputs is no more than two to six output clock cycles.

2.7. OE Deassertion

When the OE pin is deasserted by making its logic low, the corresponding DIFF output is stopped cleanly, and the final output state is driven low.

2.8. SSON Clarification

SSON is an active input used to enable -0.5% spread on all DIFF outputs. When sampled high, -0.5% spread is enabled on all DIFF outputs. When sampled low, the DIFF output frequencies are non-spread.



3. Test and Measurement Setup

This diagram shows the test load configuration for the differential clock signals.

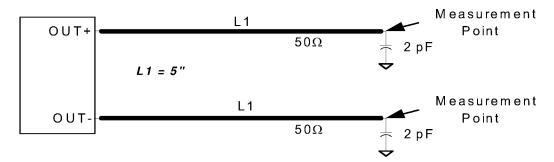


Figure 3. 0.7 V Differential Load Configuration

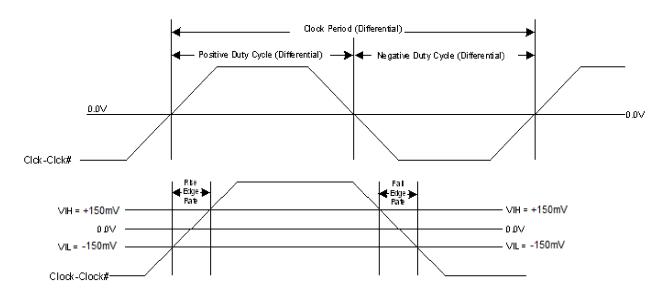


Figure 4. Differential Output Signals (for AC Parameters Measurement)

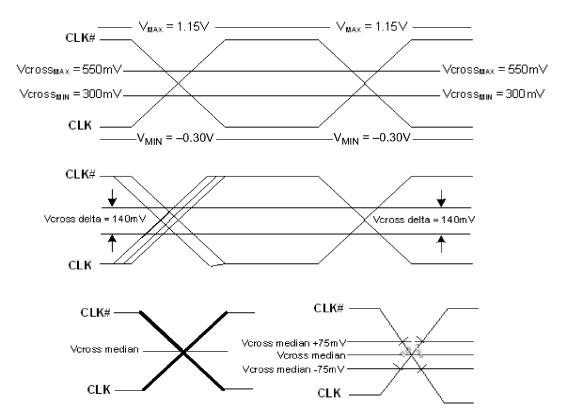


Figure 5. Single-ended Measurement for Differential Output Signals (for AC Parameters Measurement)



4. Control Registers

4.1. Serial Data Interface

To enhance the flexibility and function of the clock synthesizer, a two-signal serial interface is provided. Through the Serial Data Interface, various device functions, such as individual clock output buffers are individually enabled or disabled. The registers associated with the Serial Data Interface initialize to their default setting at power-up. The use of this interface is optional. Clock device register changes are normally made at system initialization, if any are required. The interface cannot be used during system operation for power management functions.

4.2. Data Protocol

The clock driver serial protocol accepts byte write, byte read, block write, and block read operations from the controller. For block write/read operation, access the bytes in sequential order from lowest to highest (most significant bit first) with the ability to stop after any complete byte is transferred. For byte write and byte read operations, the system controller can access individually indexed bytes. The offset of the indexed byte is encoded in the command code described in Table 1 on page 4.

The block write and block read protocol is outlined in Table 5 while Table 6 outlines byte write and byte read protocol. The slave receiver address is 11010110 (D6h).

Table 5. Block Read and Block Write Protocol

	Block Write Protocol		Block Read Protocol
Bit	Description	Bit	Description
1	Start	1	Start
8:2	Slave address—7 bits	8:2	Slave address—7 bits
9	Write	9	Write
10	Acknowledge from slave	10	Acknowledge from slave
18:11	Command Code—8 bits	18:11	Command Code–8 bits
19	Acknowledge from slave	19	Acknowledge from slave
27:20	Byte Count—8 bits	20	Repeat start
28	Acknowledge from slave	27:21	Slave address—7 bits
36:29	Data byte 1–8 bits	28	Read = 1
37	Acknowledge from slave	29	Acknowledge from slave
45:38	Data byte 2–8 bits	37:30	Byte Count from slave—8 bits
46	Acknowledge from slave	38	Acknowledge
	Data Byte/Slave Acknowledges	46:39	Data byte 1 from slave—8 bits
	Data Byte N–8 bits	47	Acknowledge
	Acknowledge from slave	55:48	Data byte 2 from slave—8 bits
	Stop	56	Acknowledge
			Data bytes from slave/Acknowledge
			Data Byte N from slave—8 bits
			NOT Acknowledge
			Stop

Table 6. Byte Read and Byte Write Protocol

	Byte Write Protocol		Byte Read Protocol
Bit	Description	Bit	Description
1	Start	1	Start
8:2	Slave address–7 bits	8:2	Slave address–7 bits
9	Write	9	Write
10	Acknowledge from slave	10	Acknowledge from slave
18:11	Command Code–8 bits	18:11	Command Code–8 bits
19	Acknowledge from slave	19	Acknowledge from slave
27:20	Data byte–8 bits	20	Repeated start
28	Acknowledge from slave	27:21	Slave address–7 bits
29	Stop	28	Read
		29	Acknowledge from slave
		37:30	Data from slave–8 bits
		38	NOT Acknowledge
		39	Stop

Control Register 0. Byte 0

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name								
Туре	R/W							

Reset settings = 00000000

В	it	Name	Function
7	:0	Reserved	

Control Register 1. Byte 1

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name				DIFF0_OE		DIFF1_OE		DIFF2_OE
Туре	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

Reset settings = 00010101

Bit	Name	Function
7:5	Reserved	
4	DIFF0_OE	Output Enable for DIFF0.
		0: Output disabled.
		1: Output Enabled.
3	Reserved	
2	DIFF1_OE	Output Enable for DIFF1.
		0: Output disabled.
		1: Output enabled.
1	Reserved	
0	DIFF2_OE	Output Enable for DIFF2.
		0: Output disabled.
		1: Output enabled.

Control Register 2. Byte 2

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name	DIFF3_OE	DIFF4_OE	DIFF5_OE					
Туре	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

Reset settings = 11100000

Bit	Name	Function
7	DIFF3_OE	Output Enable for DIFF3. 0: Output disabled. 1: Output enabled.
6	DIFF4_OE	Output Enable for DIFF4. 0: Output disabled. 1: Output enabled.
5	DIFF5_OE	Output Enable for DIFF5. 0: Output disabled. 1: Output enabled.
4:0	Reserved	

Control Register 3. Byte 3

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name		Rev Co	de[3:0]		Vendor ID[3:0]			
Туре	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

Reset settings = 00001000

Bit	Name	Function			
7:4	Rev Code[3:0]	Program Revision Code.			
3:0	Vendor ID[3:0]	Vendor Identification Code.			



Control Register 4. Byte 4

Bit	D7	D6	D6 D5 D4		D3	D2	D1	D0	
Name	BC[7:0]								
Туре	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W	

Reset settings = 00000110

Bit	Name	Function
7:0	BC[7:0]	Byte Count Register.

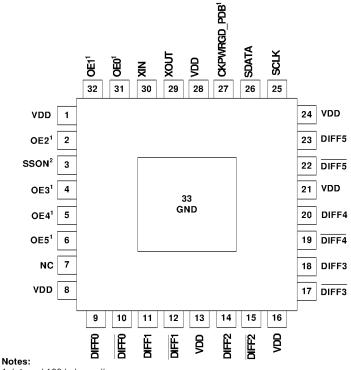
Control Register 5. Byte 5

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name	DIFF_Amp_Sel	DIFF_Amp_Cntl[2]	DIFF_Amp_Cntl[1]	DIFF_Amp_Cntl[0]				
Туре	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

Reset settings = 11011000

Bit	Name	Function				
7	DIFF_Amp_Sel	Amplitude Control for DIFF Differential Outputs. 0: Differential outputs with Default amplitude. 1: Differential outputs amplitude is set by Byte 5[6:4].				
6	DIFF_Amp_Cntl[2]	DIFF Differential Outputs Amplitude Adjustment.				
5	DIFF_Amp_Cntl[1]	000: 300 mV 001: 400 mV 010: 500 mV 011: 600 mV				
4	DIFF_Amp_Cntl[0]	100: 700 mV 101: 800 mV 110: 900 mV 111: 1000 mV				
3:0	Reserved					

5. Pin Descriptions: 32-Pin QFN



Internal 100 kohm pull-up.
 Internal 100 kohm pull-down.

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Pin #	Name	Туре	Description
1	VDD	PWR	3.3 V power supply
2	OE2	I,PU	3.3 V input to disable DIFF2 (internal 100 k Ω pull-up). Refer to Table 1 on page 4 for OE specifications.
3	SSON	I, PD	3.3 V-tolerant input for enabling –0.5% spread on DIFF clocks (internal 100 k Ω pull-down)
4	OE3	I,PU	3.3 V input to disable DIFF3 (internal 100 k Ω pull-up). Refer to Table 1 on page 4 for OE specifications.
5	OE4	I,PU	3.3 V input to disable DIFF4 (internal 100 k Ω pull-up). Refer to Table 1 on page 4 for OE specifications.
6	OE5	I,PU	3.3 V input to disable DIFF5 (internal 100 k Ω pull-up). Refer to Table 1 on page 4 for OE specifications.
7	NC	NC	No connect
8	VDD	PWR	3.3 V power supply
9	DIFF0	O, DIF	0.7 V, 100 MHz differential clock
10	DIFF0	O, DIF	0.7 V, 100 MHz differential clock
11	DIFF1	O, DIF	0.7 V, 100 MHz differential clock

Table 7. Si52146 32-Pin QFN Descriptions

Table 7. Si52146 32-Pin QFN Descriptions

Pin #	Name	Туре	Description
12	DIFF1	O, DIF	0.7 V, 100 MHz differential clock
13	VDD	PWR	3.3 V power supply
14	DIFF2	O, DIF	0.7 V, 100 MHz differential clock
15	DIFF2	O, DIF	0.7 V, 100 MHz differential clock
16	VDD	PWR	3.3 V power supply
17	DIFF3	O, DIF	0.7 V, 100 MHz differential clock
18	DIFF3	O, DIF	0.7 V, 100 MHz differential clock
19	DIFF4	O, DIF	0.7 V, 100 MHz differential clock
20	DIFF4	O, DIF	0.7 V, 100 MHz differential clock
21	VDD	PWR	3.3 V power supply
22	DIFF5	O, DIF	0.7 V, 100 MHz differential clock
23	DIFF5	O, DIF	0.7 V, 100 MHz differential clock
24	VDD	PWR	3.3 V power supply
25	SCLK	1	SMBus compatible SCLOCK
26	SDATA	I/O	SMBus compatible SDATA
27	CKPWRGD_PDB	I, PU	3.3 V CMOS input. A real-time active low input for asserting power down (PDB) and disabling all outputs (internal 100 k Ω pull-up).
28	VDD	PWR	3.3 V power supply
29	XOUT	0	25.00 MHz crystal output, Float XOUT if using only CLKIN (clock input)
30	XIN/CLKIN	I	25.00 MHz crystal input or 3.3 V, 25 MHz clock input
31	OE0	I,PU	3.3 V input to disable DIFF0 (internal 100 k Ω pull-up). Refer to Table 1 on page 4 for OE specifications.
32	OE1	I,PU	3.3 V input to disable DIFF1 (internal 100 k Ω pull-up). Refer to Table 1 on page 4 for OE specifications.
33	GND	GND	Ground for bottom pad of the IC.

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6. Ordering Guide

Part Number	Package Type	Temperature
Lead-free		
Si52146-A01AGM	32-pin QFN	Industrial, –40 to 85 °C
Si52146-A01AGMR	32-pin QFN—Tape and Reel	Industrial, –40 to 85 °C



7. Package Outline

Figure 6 illustrates the package details for the Si52146. Table 8 lists the values for the dimensions shown in the illustration.

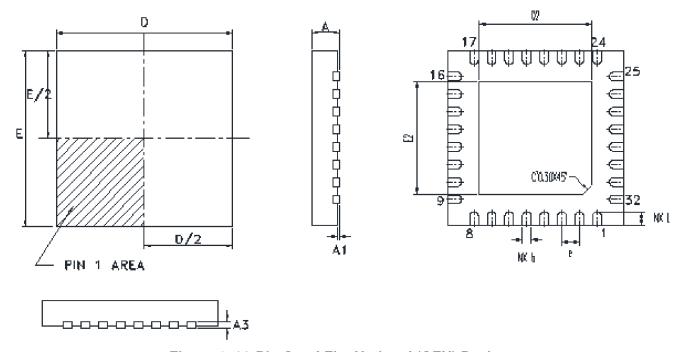


Figure 6. 32-Pin Quad Flat No Lead (QFN) Package

Table 8. Package Diagram Dimensions

Symbol	Millimeters				
	Min	Nom	Max		
A	0.70	0.75	0.80		
A1	0.00	0.02	0.05		
A3	0.175	0.20	0.225		
b	0.20	0.25	0.30		
D	4.90	5.00	5.10		
D2	3.15	3.20	3.25		
е		0.50 BSC			
E	4.90	5.00	5.10		
E2	3.15	3.20	3.25		
L	0.30	0.40	0.50		

Notes:

- All dimensions shown are in millimeters (mm) unless otherwise noted.
- **2.** Dimensioning and Tolerancing per ANSI Y14.5M-1994.
- **3.** Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.
- 4. Coplanarity less than 0.08 mm.
- 5. Terminal #1 identifier and terminal numbering convention conform to JESD 95-1 SPP-012.



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